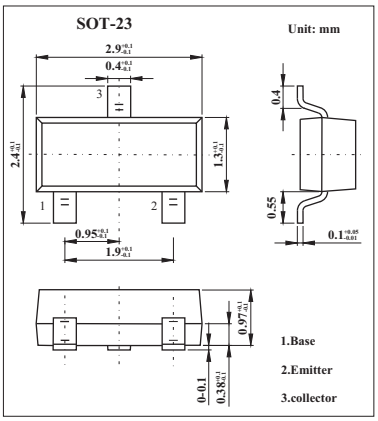
PNP Silicon Transistors

KTA1298



Features

Collector Power Dissipation: P_C=200mW

Collector Current: I_C=-800mA

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	-35	V
Collector-Base Voltage	V_{CBO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1mA,I_E=0	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA,I_C=0	-5			V
Collector Cut-off Current	I_{CBO}	V_{CB}=-30V, I_E=0			-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.1	μA
DC Current Gain	h_{FE}	V_{CE}=-1V, I_C=-100mA	100		320	
		V_{CE}=-1V, I_C=-800mA	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-20mA			-0.4	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-10mA		120		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		13		pF

h_{FE} Classification

Marking	IO	IY
Rank	O	Y
h_{FE}	100 200	160 320